

# MA2S304

## Silicon epitaxial planar type

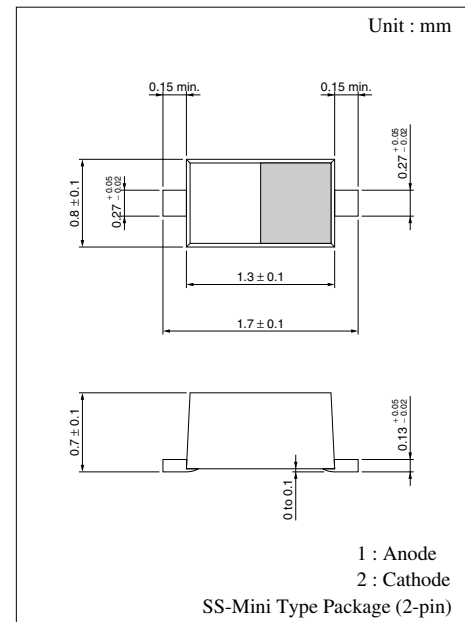
For VCO

### ■ Features

- Good linearity and large capacitance-ratio in  $C_D - V_R$  relation
- Small series resistance  $r_D$
- SS-mini type package, allowing downsizing of equipment and automatic insertion through the taping package

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	30	V
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: K

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 28\text{ V}$			10	nA
Diode capacitance	$C_{D(1V)}$	$V_R = 1\text{ V}, f = 1\text{ MHz}$	24.8		29.8	pF
	$C_{D(4V)}$	$V_R = 4\text{ V}, f = 1\text{ MHz}$	6.0		8.3	pF
Capacitance ratio	$C_{D(1V)}/C_{D(4V)}$		3.0			—
Series resistance*	$r_D$	$V_R = 4\text{ V}, f = 100\text{ MHz}$			1.0	$\Omega$

Note) 1. Rated input/output frequency: 100 MHz

2. \*:  $r_f$  measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

